



MMBT2907AW

PNP GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 60 Volts **POWER** 225 mW

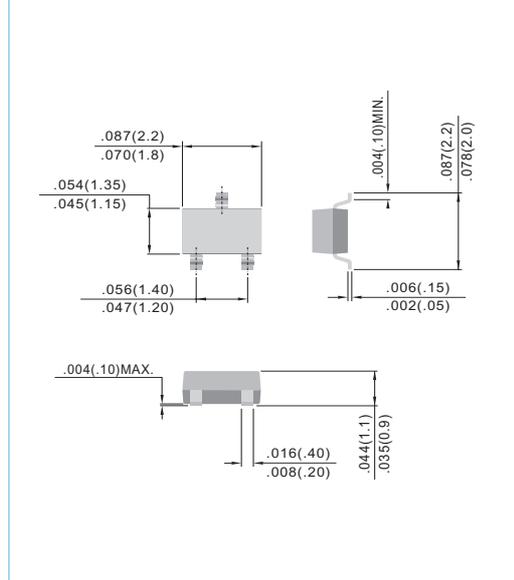
SOT-323 Unit: inch (mm)

FEATURES

PNP epitaxial silicon, planar design
 Collector-emitter voltage $V_{CE} = -60V$
 Collector current $I_C = -600mA$
 In compliance with EU RoHS 2002/95/EC directives and with Halogen Free

MECHANICAL DATA

Case: SOT-323
 Terminals : Solderable per MIL-STD-750,Method 2026
 Approx Weight: 0.0048 gram
 Device Marking : M7A



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Collector-Emitter Voltage	V_{CEO}	-60	V
Collector-Base Voltage	V_{CBO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-600	mA

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	225	mW
Storage Temperature	T_{STG}	-55 to 150	°C
Junction Temperature	T_J	-55 to 150	°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C / W

Note 1 : Transistor mounted on FR-5 board 1.0 x 0.75 x 0.062 in.



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ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C = -10mA, I _B = 0	-60	-	-	V
Collector-Base Breakdown Voltage	V _(BR) CBO	I _C = -10μA, I _E = 0	-60	-	-	V
Emitter-Base Breakdown Voltage	V _(BR) EBO	I _E = -10μA, I _C = 0	-5.0	-	-	V
Base Cutoff Current	I _{BL}	V _{CE} = -30V, V _{EB} = -0.5V	-	-	-50	nA
Collector Cutoff Current	I _{CEX}	V _{CE} = -30V, V _{EB} = -0.5V	-	-	-50	nA
	I _{CBO}	V _{CE} = -50V, I _E = 0	-	-	-10	nA
		V _{CE} = -50V, I _E = 0 T _J = 125°C	-	-	-10	μA
DC Current Gain	h _{FE}	I _C = -0.1mA, V _{CE} = -10V	75	-	-	-
		I _C = -1.0mA, V _{CE} = -10V	100	-	-	-
		I _C = -10mA, V _{CE} = -10V	100	-	-	-
		I _C = -150mA, V _{CE} = -10V	100	-	-	300
		I _C = -500mA, V _{CE} = -10V	50	-	-	-
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C = -150mA, I _B = -15mA	-	-	-0.4	V
		I _C = -500mA, I _B = -50mA	-	-	-1.6	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C = -150mA, I _B = -15mA	-	-	-1.3	V
		I _C = -500mA, I _B = -50mA	-	-	-2.6	V
Collector-Base Capacitance	C _{CB0}	V _{CB} = -10V, I _E = 0, f = 1MHz	-	-	8.0	pF
Emitter-Base Capacitance	C _{EBO}	V _{CB} = -2V, I _C = 0, f = 1MHz	-	-	30	pF
Current Gain-Bandwidth Product	F _T	I _C = -50mA, V _{CE} = -20V, f = 100MHz	200	-	-	MHz
Turn-On Time	t _{on}	V _{CC} = -30V, V _{BE} = -0.5V, I _C = -150mA, I _B = -15mA	-	-	45	ns
Delay Time	t _d	V _{CC} = -30V, V _{BE} = -0.5V, I _C = -150mA, I _B = -15mA	-	-	10	ns
Rise Time	t _r	V _{CC} = -30V, V _{BE} = -0.5V, I _C = -150mA, I _{B1} = -15mA	-	-	40	ns
Turn-Off Time	t _{off}	V _{CC} = -6V, I _C = -150mA, I _{B1} = I _{B2} = -15mA	-	-	100	ns
Storage Time	t _s	V _{CC} = -6V, I _C = -150mA, I _{B1} = I _{B2} = -15mA	-	-	80	ns
Fall Time	t _f	V _{CC} = -6V, I _C = -150mA, I _{B1} = I _{B2} = -15mA	-	-	30	ns



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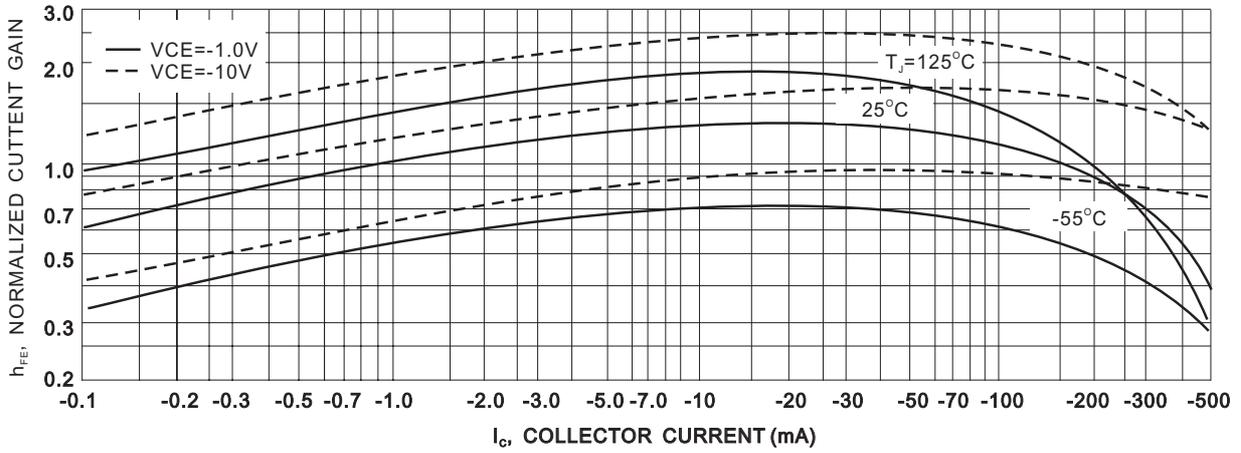


Fig.1-DC Current Gain

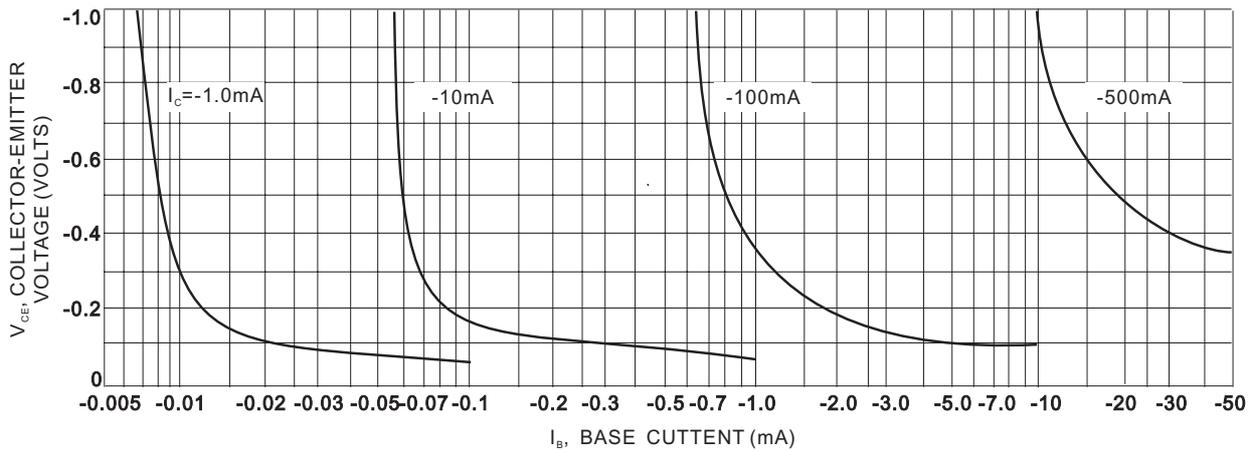


Fig.2-Collector Saturation Region

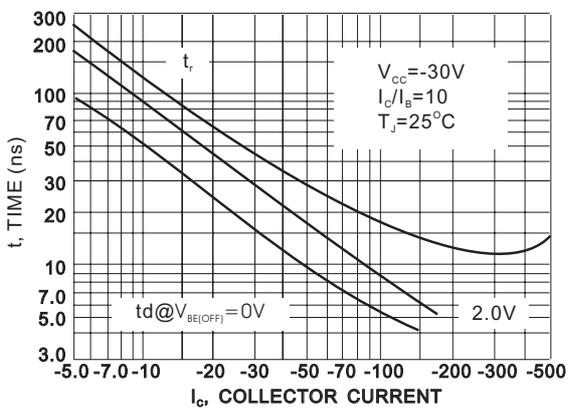


Fig.3-Turn-On Time

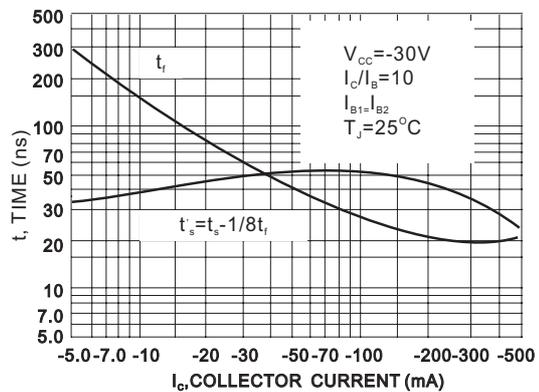


Fig.4-Turn-Off Time



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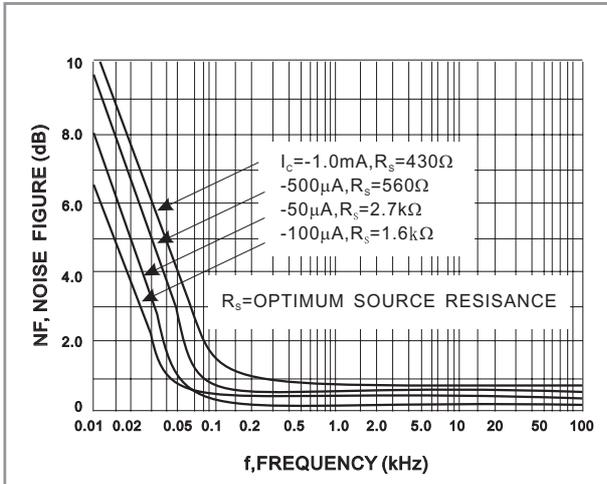


Fig.5-Frequency Effects

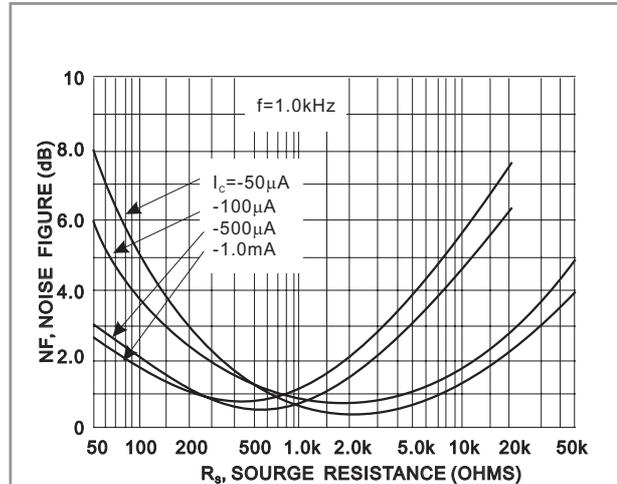


Fig.6-Source Resistance Effects

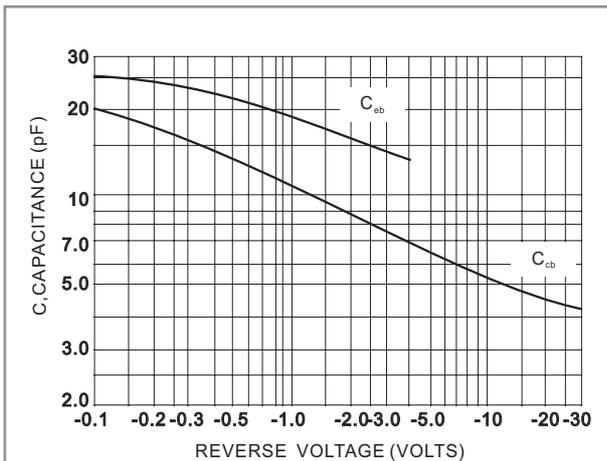


Fig.7-Capacitances

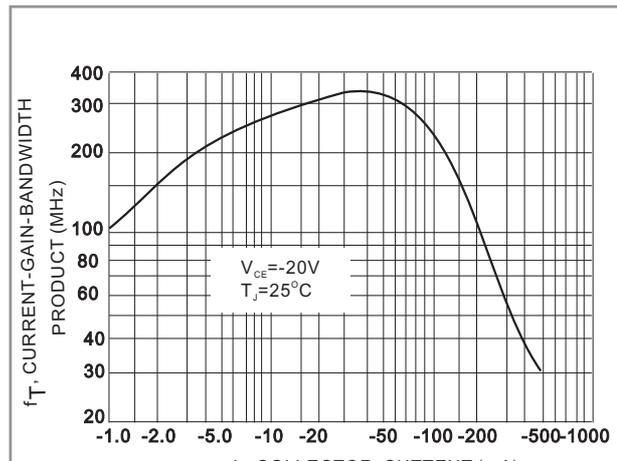


Fig.8-Current-Gain-Bandwidth Product

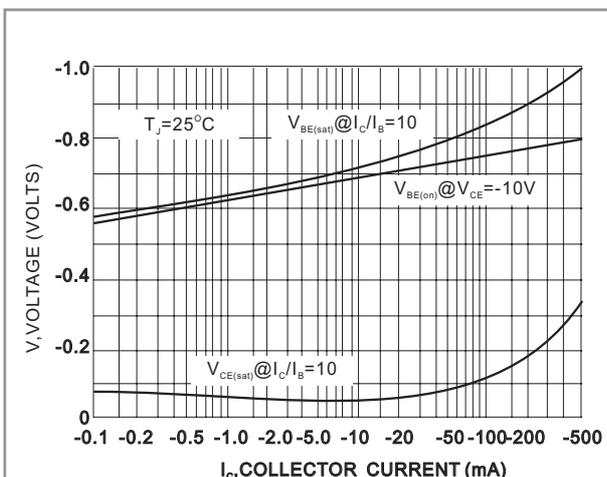


Fig.9-On Voltage

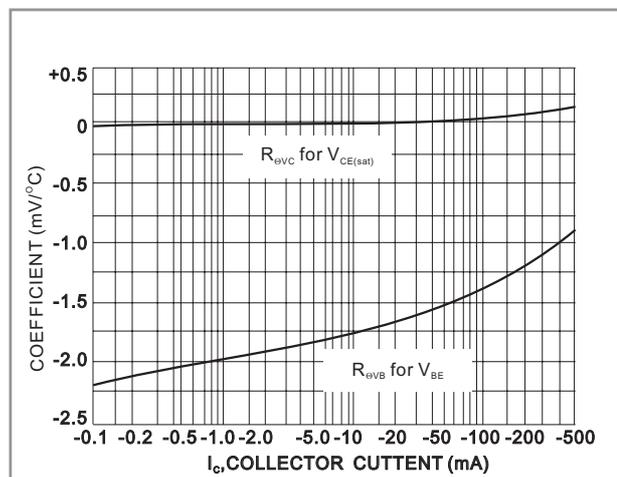
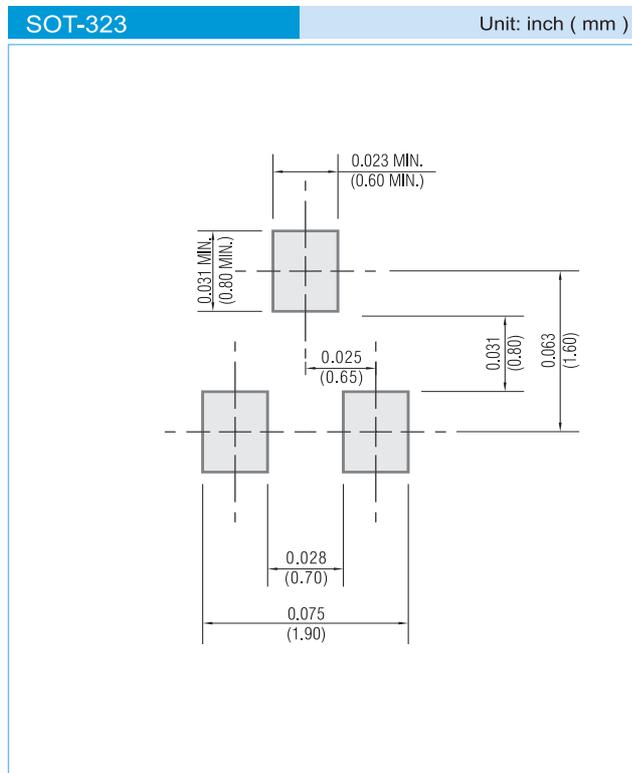


Fig.10-Temperature Coefficients



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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information

T/R - 12K per 13" plastic Reel

T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

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